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(54) **THIN FILM TRANSISTOR AND DISPLAY APPARATUS COMPRISING THE SAME**

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(57) **ABSTRACT**

A thin film transistor including an active layer; and a gate electrode at least partially overlapped with the active layer. Further, the active layer includes a first active layer and a second active layer on the first active layer; a channel; a first connection portion contacting a first side of the channel; and a second connection portion contacting a second side of the channel. In addition, the channel includes a first overlap area in which the first active layer and the second active layer overlap each other based on a plan view; and a first non-overlap area in which the first active layer and the second active layer do not overlap each other based on the plan view. Also, in the channel of the active layer, each of the first active layer and the second active layer extends from the first connection portion to the second connection portion. The second active layer also has a mobility greater than a mobility of the first active layer.

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